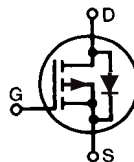


TrenchP™ Power MOSFET

IXTA28P065T
IXTP28P065T

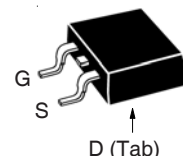
$$\begin{aligned} V_{DSS} &= -65V \\ I_{D25} &= -28A \\ R_{DS(on)} &\leq 45m\Omega \end{aligned}$$

P-Channel Enhancement Mode
Avalanche Rated

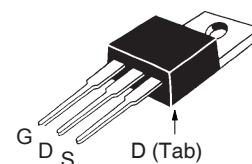


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	- 65	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GS} = 1M\Omega$	- 65	V
V_{GSS}	Continuous	± 15	V
V_{GSM}	Transient	± 25	V
I_{D25}	$T_C = 25^\circ\text{C}$	- 28	A
I_{DM}	$T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM}	- 90	A
I_{AR}	$T_C = 25^\circ\text{C}$	- 28	A
E_S	$T_C = 25^\circ\text{C}$	200	mJ
P_D	$T_C = 25^\circ\text{C}$	83	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6mm (0.062 in.) from Case for 10s	300	$^\circ\text{C}$
T_{SOLD}	Plastic Body for 10s	260	$^\circ\text{C}$
M_d	Mounting Torque (TO-220)	1.13 / 10	Nm/lb.in.
Weight	TO-220	3.0	g
	TO-263	2.5	g

TO-263 AA (IXTA)



TO-220AB (IXTP)



G = Gate D = Drain
S = Source Tab = Drain

Features

- International Standard Packages
- Avalanche Rated
- Extended FBSOA
- Fast Intrinsic Diode
- Low $R_{DS(ON)}$ and Q_G

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- High-Side Switching
- Push Pull Amplifiers
- DC Choppers
- Automatic Test Equipment
- Current Regulators
- Battery Charger Applications

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = -250\mu A$	- 65		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\mu A$	- 2.5		V
I_{GSS}	$V_{GS} = \pm 15V$, $V_{DS} = 0V$			± 50 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ\text{C}$			- 3 μA -100 μA
$R_{DS(on)}$	$V_{GS} = -10V$, $I_D = 0.5 \cdot I_{D25}$, Note 1			45 m Ω

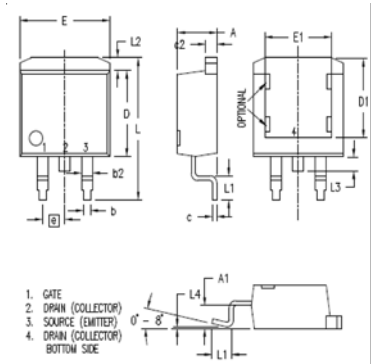
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = -10\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1	10	16	S
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = -25\text{V}$, $f = 1\text{MHz}$		2030	pF
C_{oss}			270	pF
C_{rss}			127	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = -10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 10\Omega$ (External)		21	ns
t_r			29	ns
$t_{d(off)}$			36	ns
t_f			23	ns
$Q_{g(on)}$	$V_{GS} = -10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$		46	nC
Q_{gs}			20	nC
Q_{gd}			10	nC
R_{thJC}	TO-220			1.5 $^\circ\text{C/W}$
R_{thCS}		0.50		$^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_s	$V_{GS} = 0\text{V}$			-28 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			-112 A
V_{SD}	$I_F = -28\text{A}$, $V_{GS} = 0\text{V}$, Note 1			-1.5 V
t_{rr}	$I_F = -14\text{A}$, $-di/dt = -100\text{A}/\mu\text{s}$ $V_R = -33\text{V}$, $V_{GS} = 0\text{V}$		31	ns
Q_{RM}			34	nC
I_{RM}			-2.2	A

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

TO-263 Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

TO-220 Outline

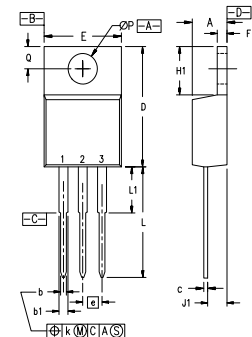


Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

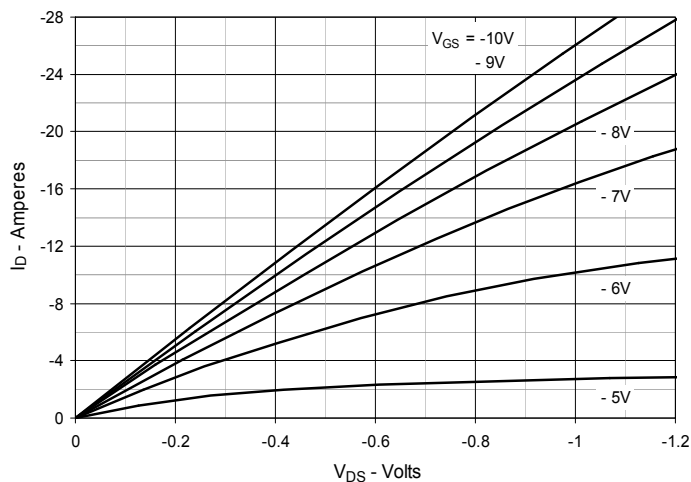


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

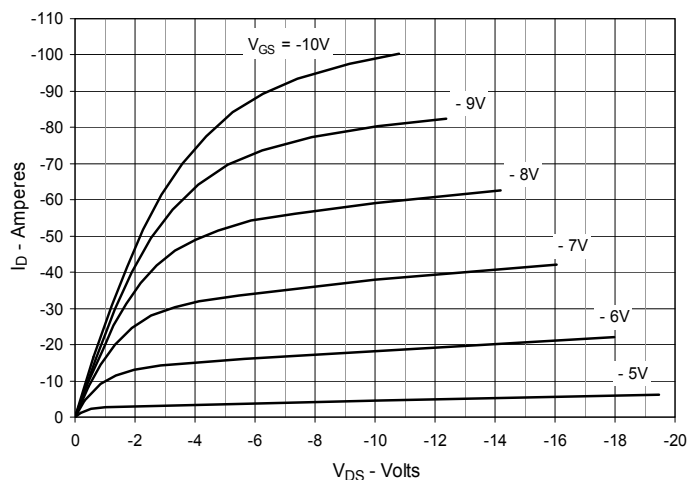


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

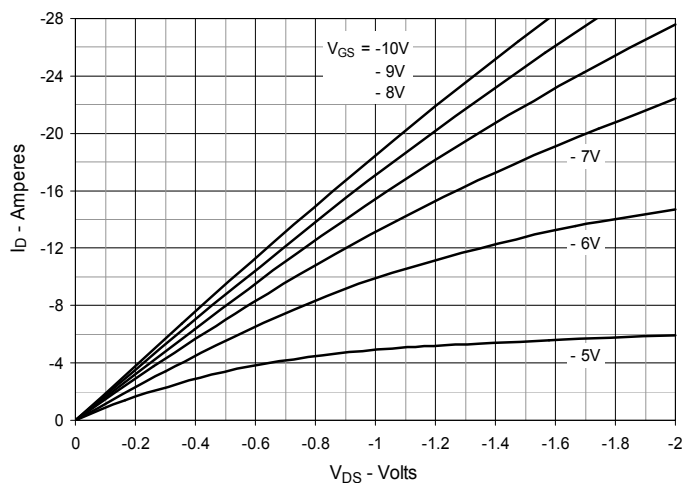


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = -14\text{A}$ vs. Junction Temperature

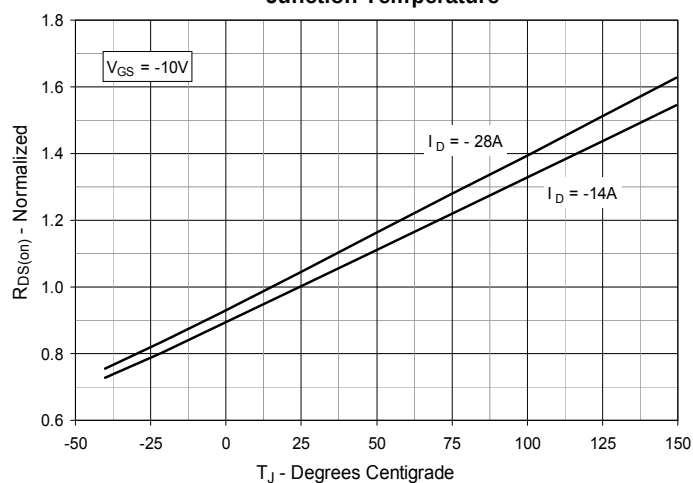


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = -14\text{A}$ vs. Drain Current

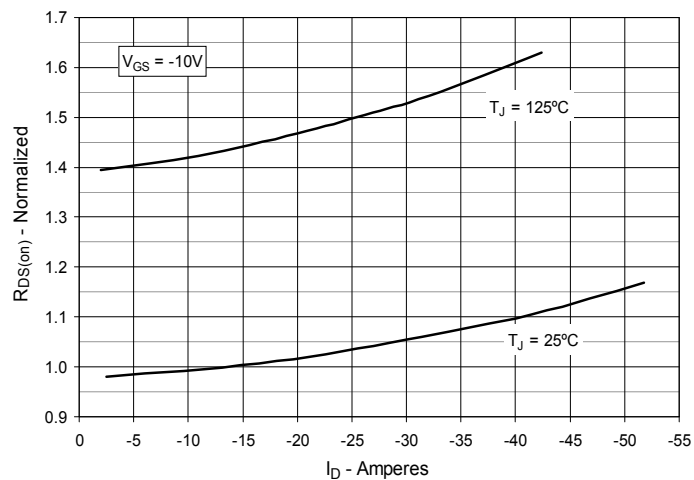


Fig. 6. Maximum Drain Current vs. Case Temperature

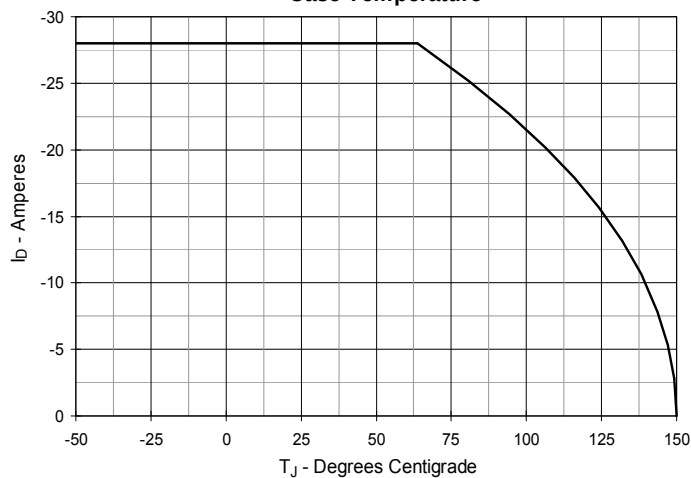


Fig. 7. Input Admittance

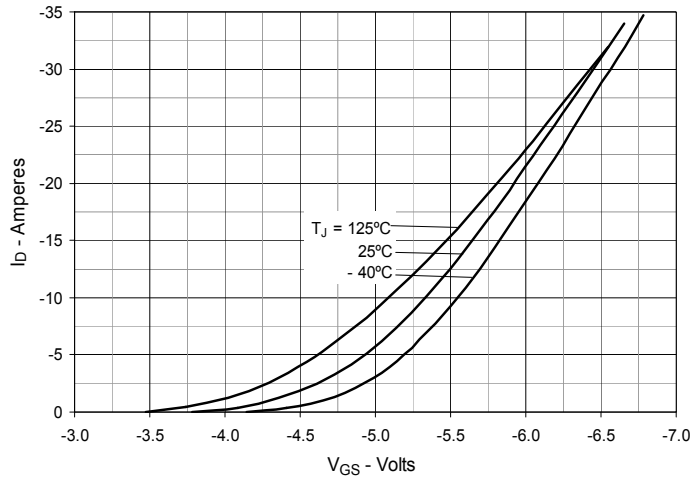


Fig. 8. Transconductance

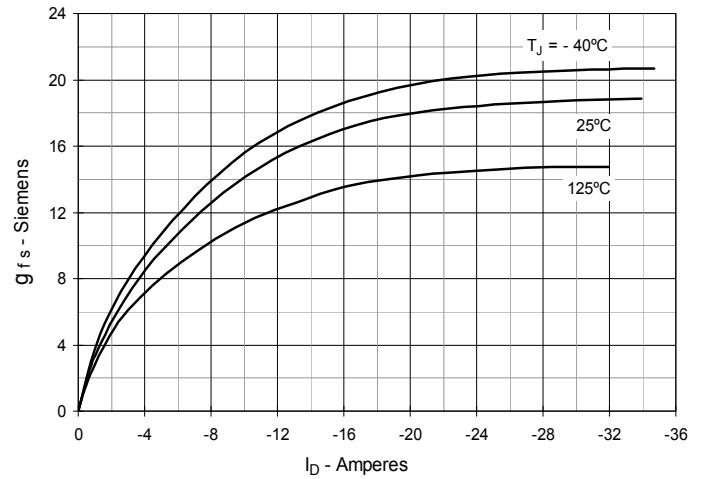


Fig. 9. Forward Voltage Drop of Intrinsic Diode

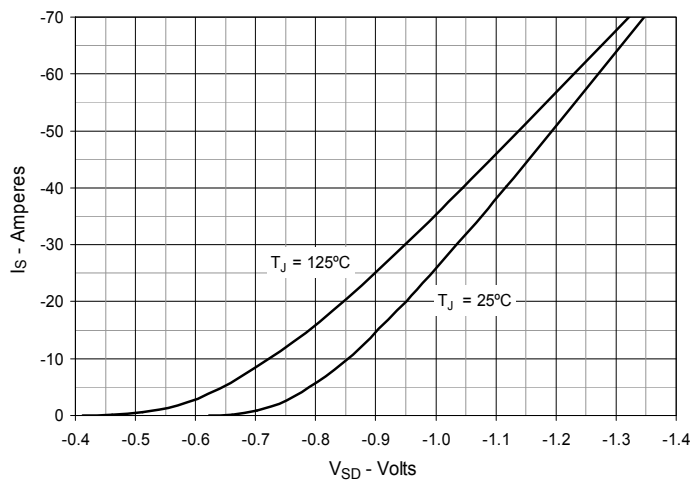


Fig. 10. Gate Charge

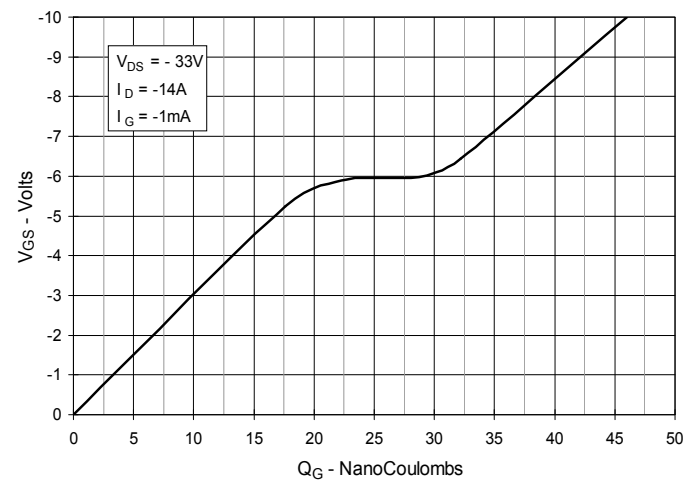


Fig. 11. Capacitance

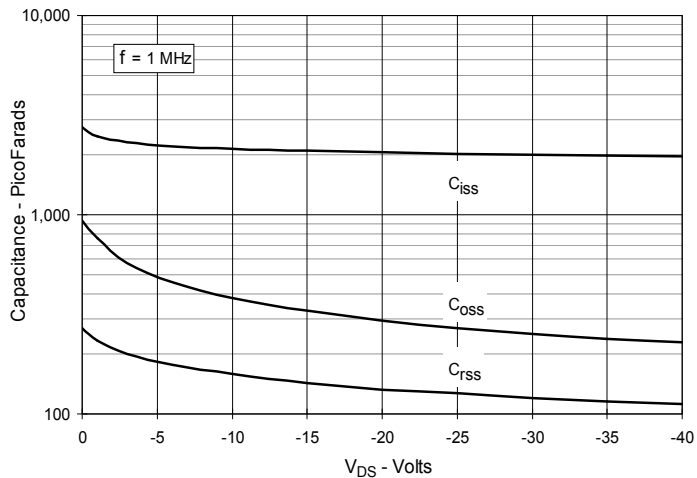


Fig. 12. Forward-Bias Safe Operating Area

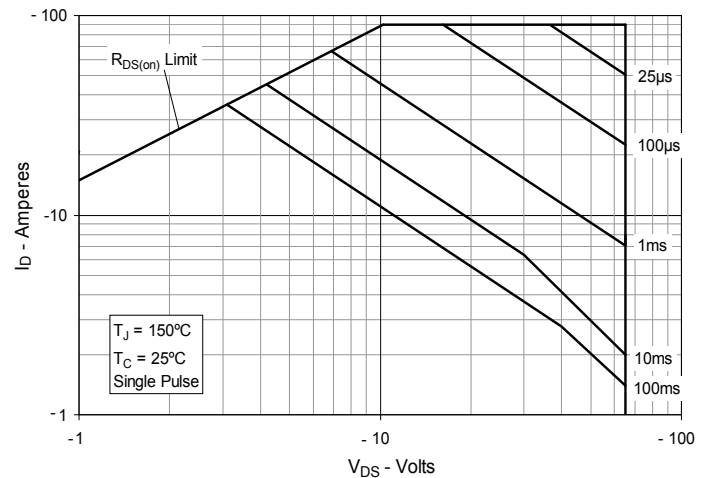


Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

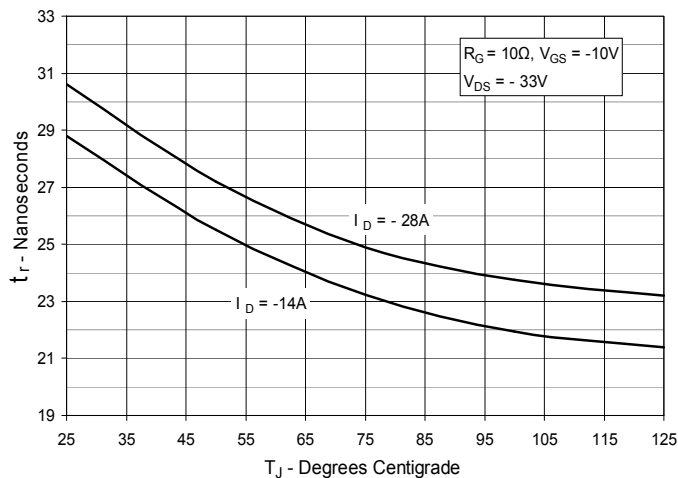


Fig. 14. Resistive Turn-on Rise Time vs. Drain Current

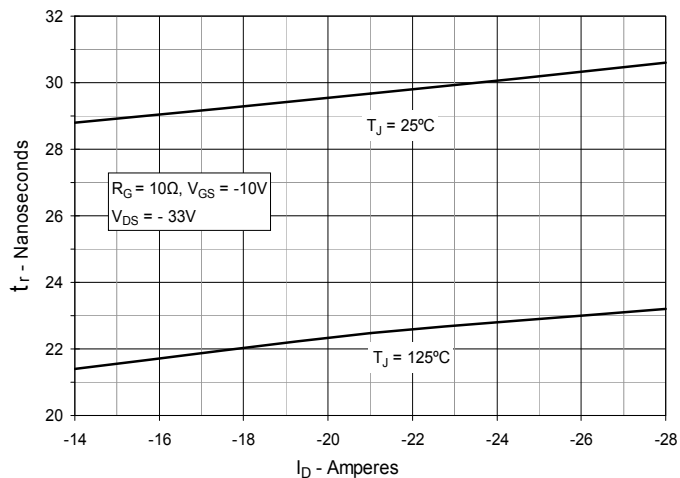


Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

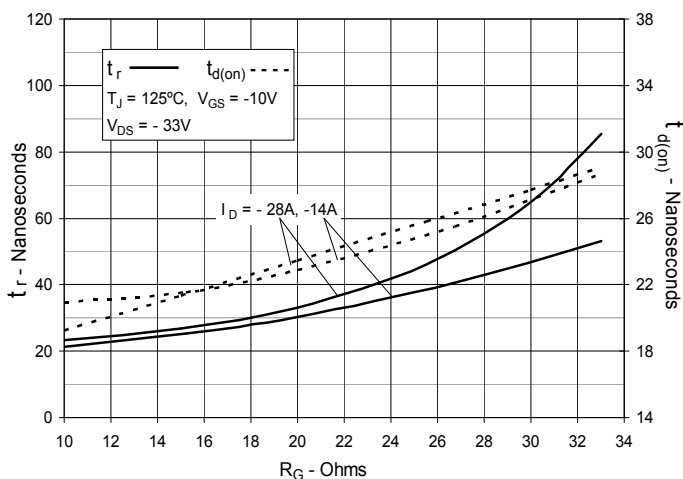


Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

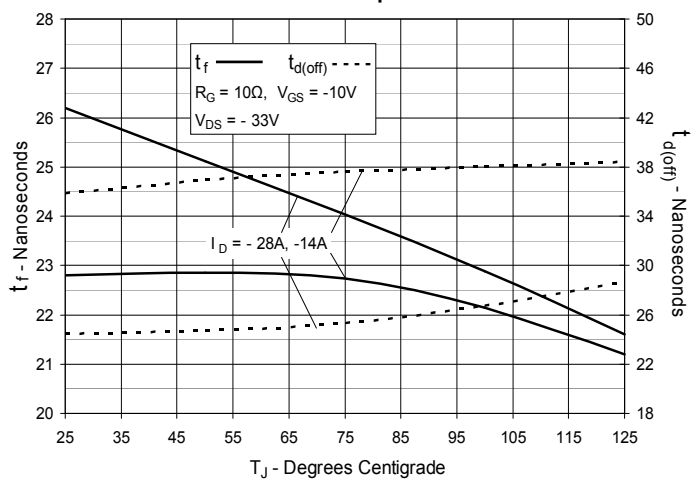


Fig. 17. Resistive Turn-off Switching Times vs. Drain Current

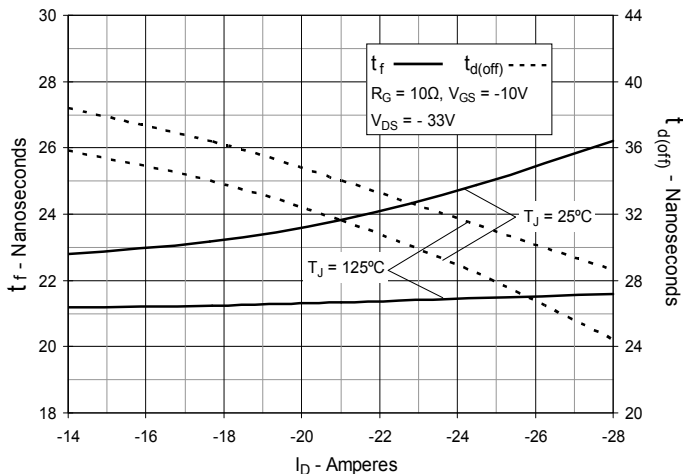


Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance

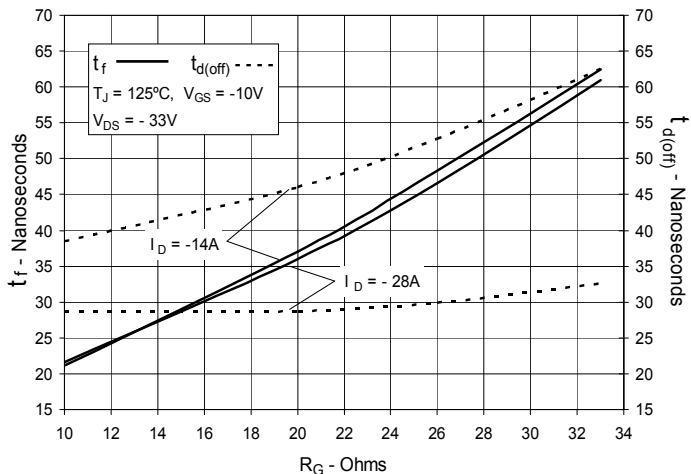


Fig. 19. Maximum Transient Thermal Impedance

